To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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HSM88ASR

Silicon Schottky Barrier Diode for Balanced Mixer

ADE-208-047D (Z)

Rev. 4
Jul. 1998

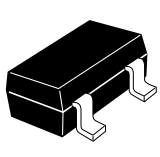
Features

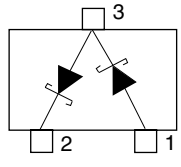
- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM88ASR	C3	MPAK

Pin Arrangement





(Top View)

1 Anode 1
2 Cathode 2
3 Cathode 1
Anode 2

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_O	15	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	350	—	420	mV	I_F = 1 mA
	V_{F2}	500	—	580		I_F = 10 mA
Reverse current	I_{R1}	—	—	0.2	µA	V_R = 2V
	I_{R2}	—	—	10		V_R = 10V
Capacitance	C	—	—	0.85	pF	V_R = 0V, f = 1 MHz
Capacitance deviation	ΔC	—	—	0.10	pF	V_R = 0V, f = 1 MHz
Forward voltage deviation	ΔV_F	—	—	10	mV	I_F = 10 mA
ESD-Capability[*1]	—	30	—	—	V	C=200pF , Both forward and reverse direction 1 pulse.

Notes 1. Failure criterion ; $I_R \geq 400$nA at V_R =2 V

Main Characteristic

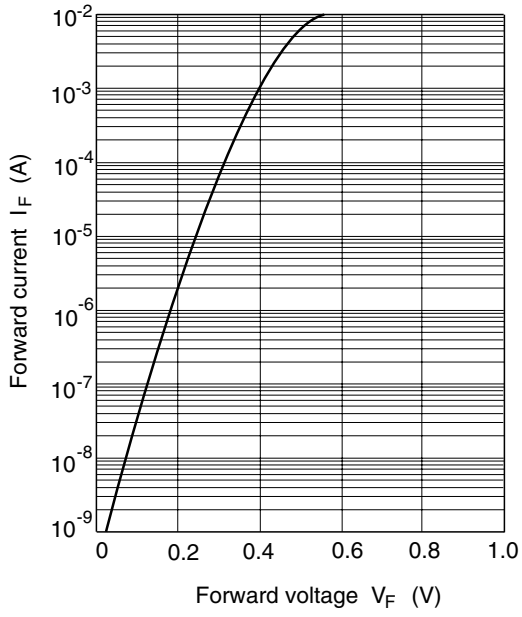


Fig.1 Forward current Vs. Forward voltage

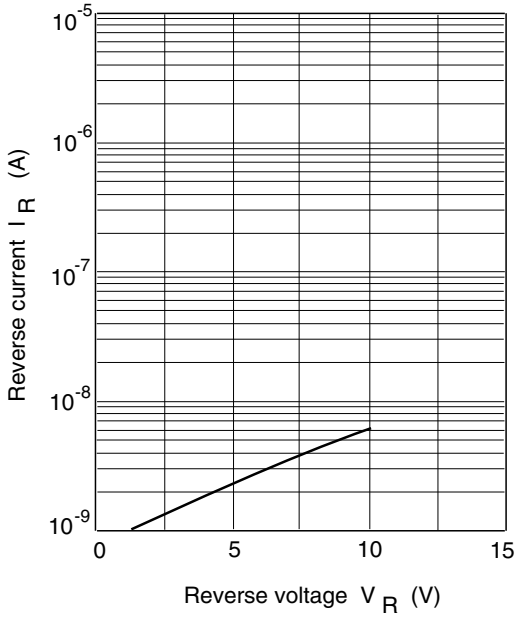


Fig.2 Reverse current Vs. Reverse voltage

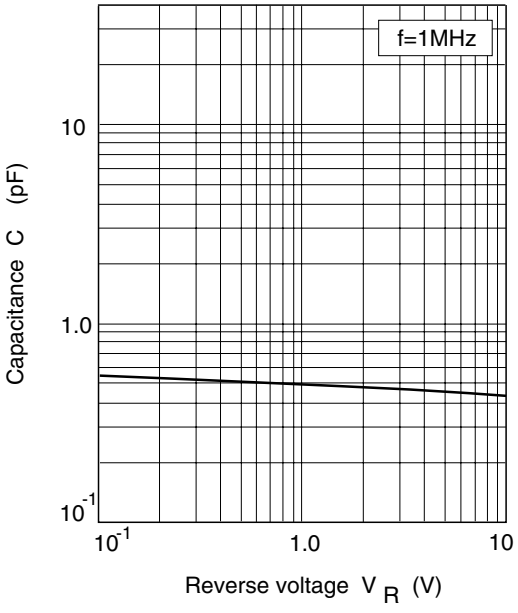
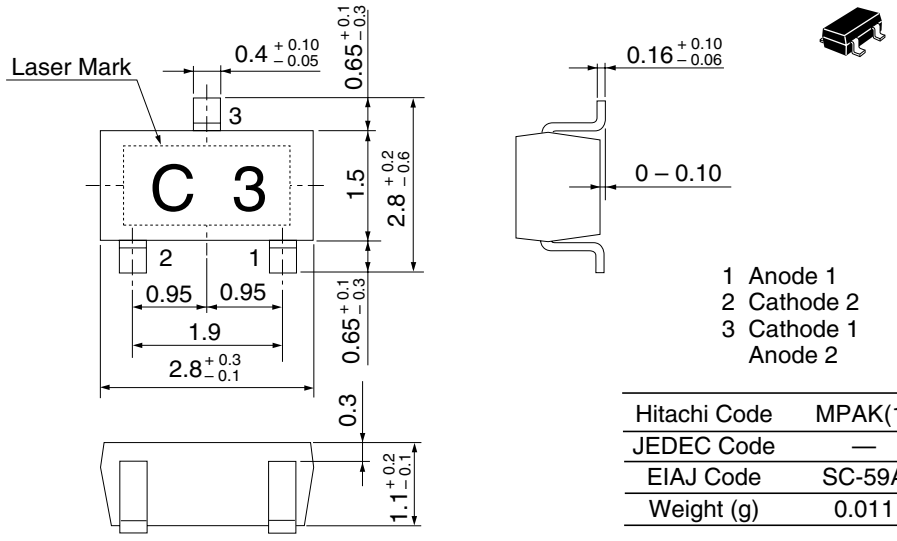


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit : mm



1 Anode 1
2 Cathode 2
3 Cathode 1
Anode 2

Hitachi Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011

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